

Complementary Silicon High-Power Transistors

...PowerBase™ complementary transistors designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc-to-dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055 and MJ2955.

- Current-Gain — Bandwidth-Product @ $I_C = 1.0 \text{ Adc}$
 $f_T = 0.8 \text{ MHz (Min) - NPN}$
 $= 2.2 \text{ MHz (Min) - PNP}$
- Safe Operating Area — Rated to 60 V and 120 V, Respectively

*MAXIMUM RATINGS

Rating	Symbol	2N3055A MJ2955A	MJ15015 MJ15016	Unit
Collector-Emitter Voltage	V_{CEO}	60	120	Vdc
Collector-Base Voltage	V_{CBO}	100	200	Vdc
Collector-Emitter Voltage Base Reversed Biased	V_{CEV}	100	200	Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Collector Current — Continuous	I_C	15		Adc
Base Current	I_B	7.0		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	115 0.65	180 1.03	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.52	0.98	$^\circ\text{C/W}$

*Indicates JEDEC Registered Data. (2N3055A)

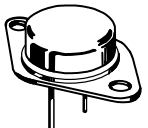
NPN
2N3055A

MJ15015 *

MJ2955A
PNP
MJ15016 *

*ON Semiconductor Preferred Device

15 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60, 120 VOLTS
115, 180 WATTS



CASE 1-07
TO-204AA
(TO-3)

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

2N3055A MJ15015 MJ2955A MJ15016

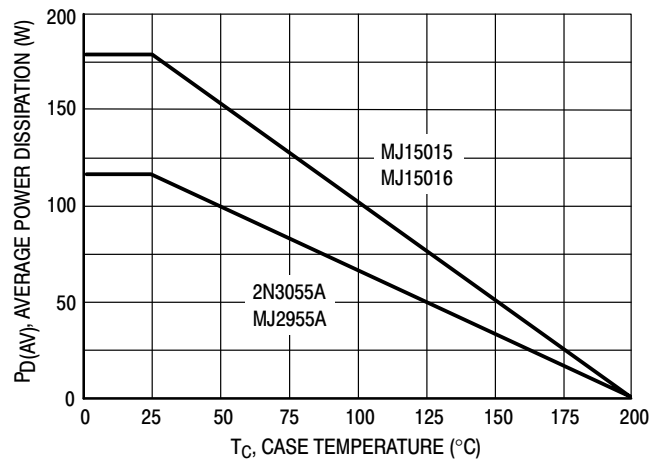


Figure 1. Power Derating

2N3055A MJ15015 MJ2955A MJ15016

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS (1)

*Collector–Emitter Sustaining Voltage ($I_C = 200\text{ mA}$, $I_B = 0$)	2N3055A, MJ2955A MJ15015, MJ15016	$V_{CEO(sus)}$	60 120	— —	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{BE(off)} = 0\text{ Vdc}$) ($V_{CE} = 60\text{ Vdc}$, $V_{BE(off)} = 0\text{ Vdc}$)	2N3055A, MJ2955A MJ15015, MJ15016	I_{CEO}	— —	0.7 0.1	mAdc
*Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$)	2N3055A, MJ2955A MJ15015, MJ15016	I_{CEV}	— —	5.0 1.0	mAdc
Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	2N3055A, MJ2955A MJ15015, MJ15016	I_{CEV}	— —	30 6.0	mAdc
Emitter Cutoff Current ($V_{EB} = 7.0\text{ Vdc}$, $I_C = 0$)	2N3055A, MJ2955A MJ15015, MJ15016	I_{EBO}	— —	5.0 0.2	mAdc

*SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased ($t = 0.5\text{ s}$ non-repetitive) ($V_{CE} = 60\text{ Vdc}$)	2N3055A, MJ2955A MJ15015, MJ15016	$I_{S/b}$	1.95 3.0	— —	Adc
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*ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 4.0\text{ Adc}$, $V_{CE} = 2.0\text{ Vdc}$) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 10\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)		h_{FE}	10 20 5.0	70 70 —	—
Collector–Emitter Saturation Voltage ($I_C = 4.0\text{ Adc}$, $I_B = 400\text{ mA}$) ($I_C = 10\text{ Adc}$, $I_B = 3.3\text{ Adc}$) ($I_C = 15\text{ Adc}$, $I_B = 7.0\text{ Adc}$)		$V_{CE(sat)}$	— — —	1.1 3.0 5.0	Vdc
Base–Emitter On Voltage ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)		$V_{BE(on)}$	0.7	1.8	Vdc

*DYNAMIC CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 1.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	2N3055A, MJ15015 MJ2955A, MJ15016	f_T	0.8 2.2	6.0 18	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)		C_{ob}	60	600	pF

*SWITCHING CHARACTERISTICS (2N3055A only)

RESISTIVE LOAD					
Delay Time	($V_{CC} = 30\text{ Vdc}$, $I_C = 4.0\text{ Adc}$, $I_{B1} = I_{B2} = 0.4\text{ Adc}$, $t_p = 25\text{ }\mu\text{s}$ Duty Cycle $\leq 2\%$)	t_d	—	0.5	μs
Rise Time		t_r	—	4.0	μs
Storage Time		t_s	—	3.0	μs
Fall Time		t_f	—	6.0	μs

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

*Indicates JEDEC Registered Data. (2N3055A)

2N3055A MJ15015 MJ2955A MJ15016

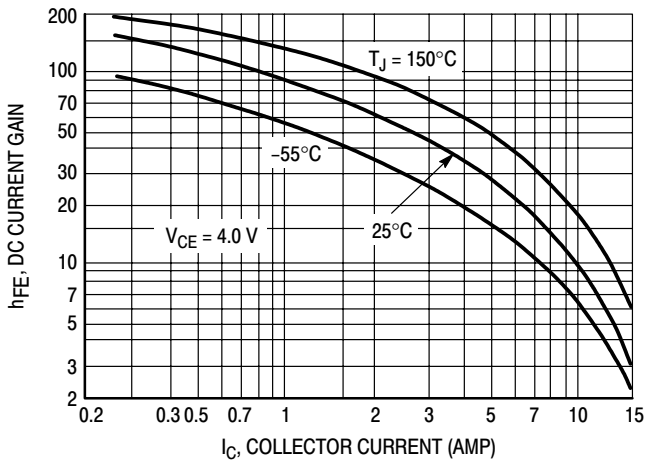


Figure 2. DC Current Gain

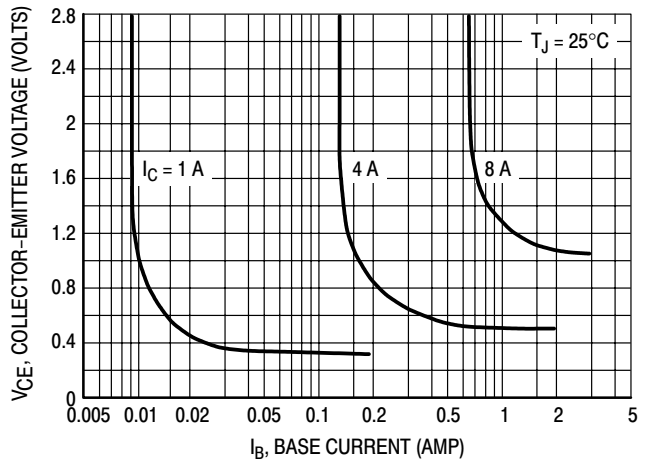


Figure 3. Collector Saturation Region

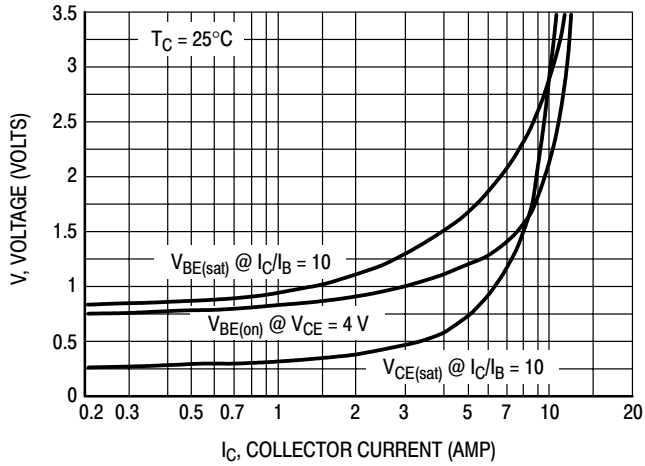


Figure 4. "On" Voltages

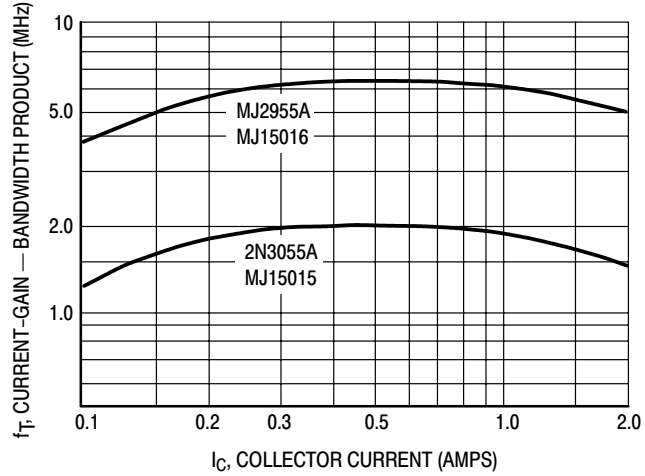


Figure 5. Current-Gain — Bandwidth Product

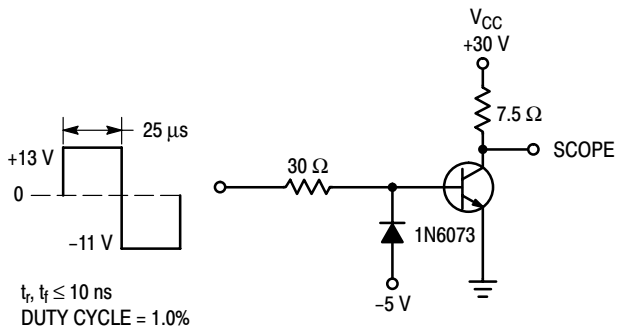


Figure 6. Switching Times Test Circuit (Circuit shown is for NPN)

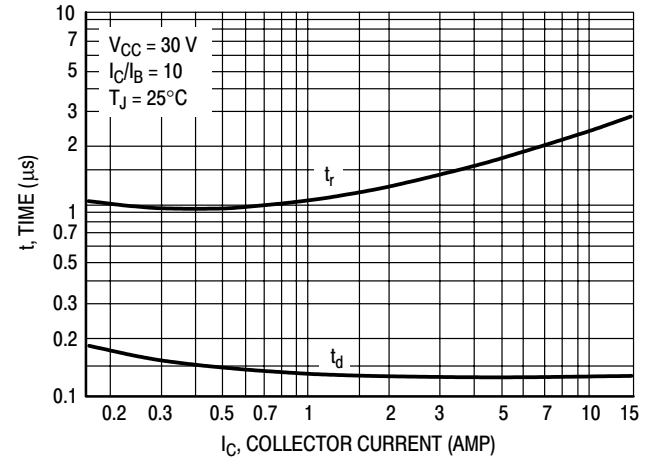


Figure 7. Turn-On Time

2N3055A MJ15015 MJ2955A MJ15016

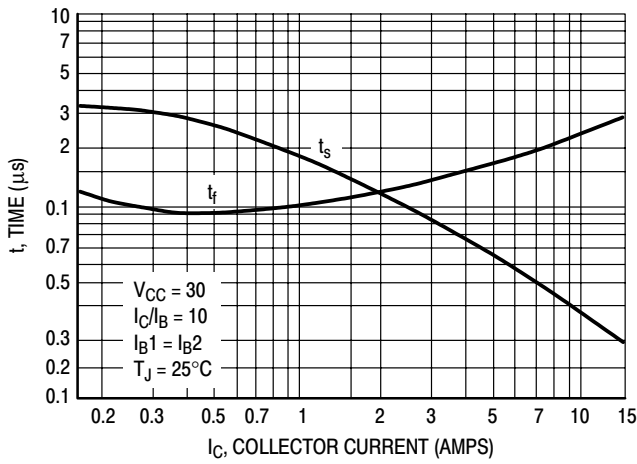


Figure 8. Turn-Off Times

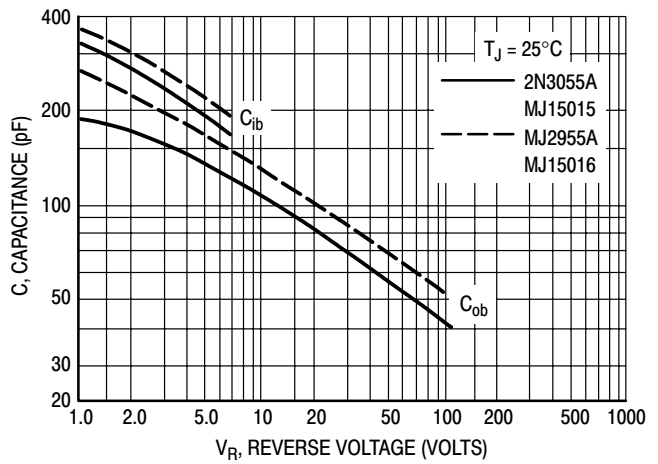


Figure 9. Capacitances

COLLECTOR CUT-OFF REGION

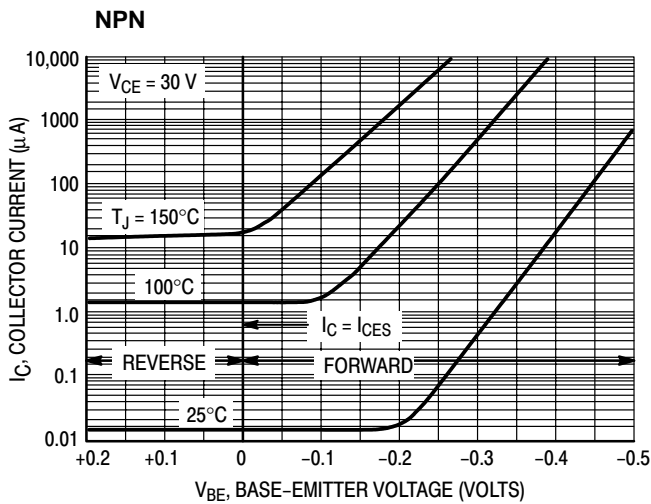


Figure 10. 2N3055A, MJ15015

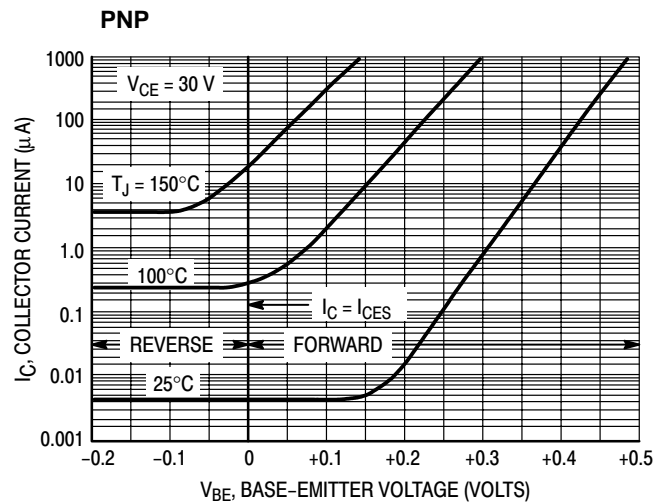


Figure 11. MJ2955A, MJ15016

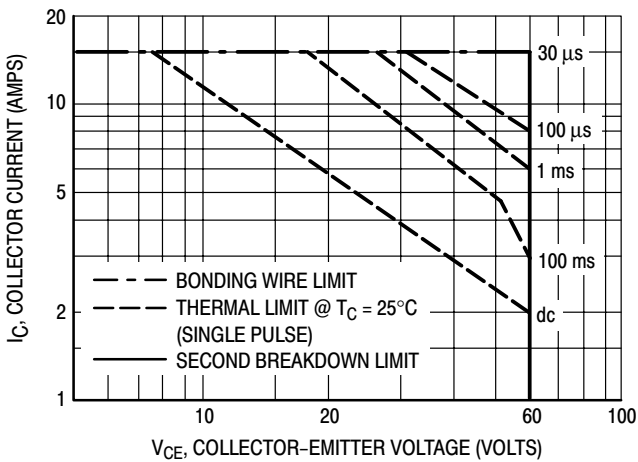


Figure 12. Forward Bias Safe Operating Area
2N3055A, MJ2955A

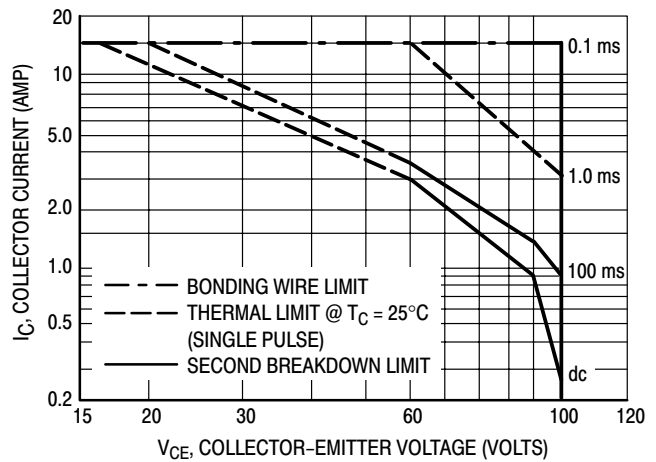


Figure 13. Forward Bias Safe Operating Area
MJ15015, MJ15016

2N3055A MJ15015 MJ2955A MJ15016

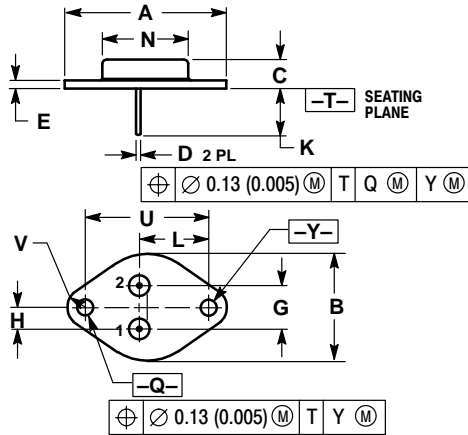
7There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 12 and 13 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

2N3055A MJ15015 MJ2955A MJ15016

PACKAGE DIMENSIONS

CASE 1-07
TO-204AA (TO-3)
ISSUE Z




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

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